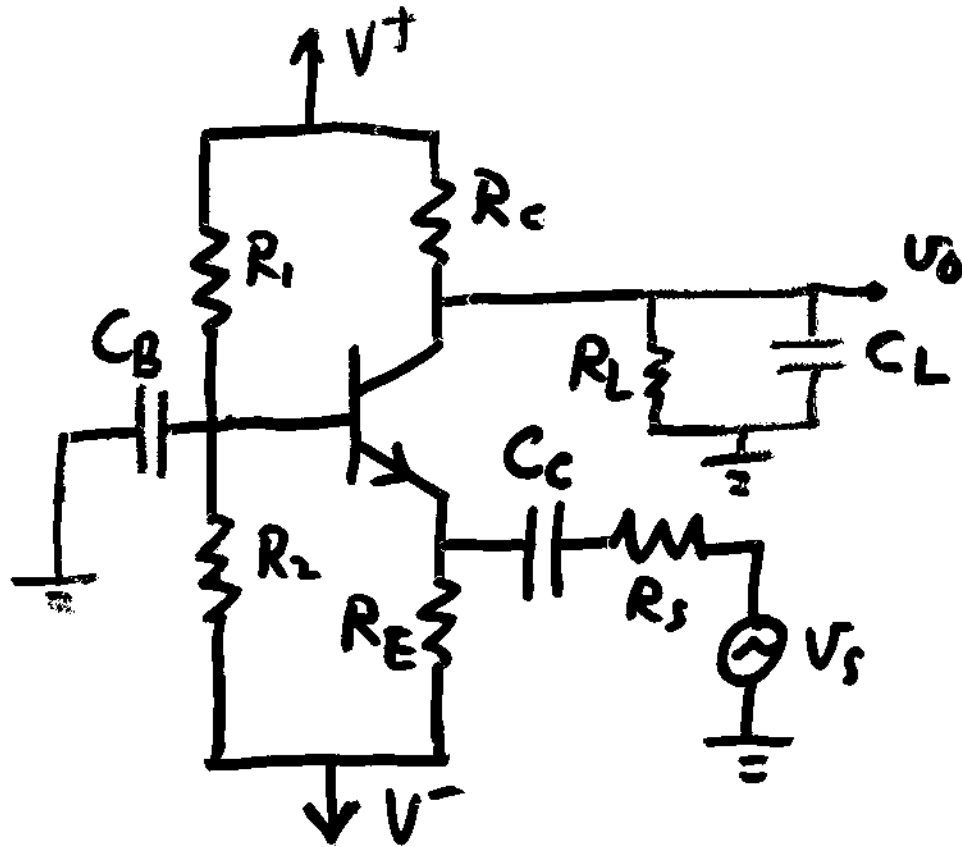
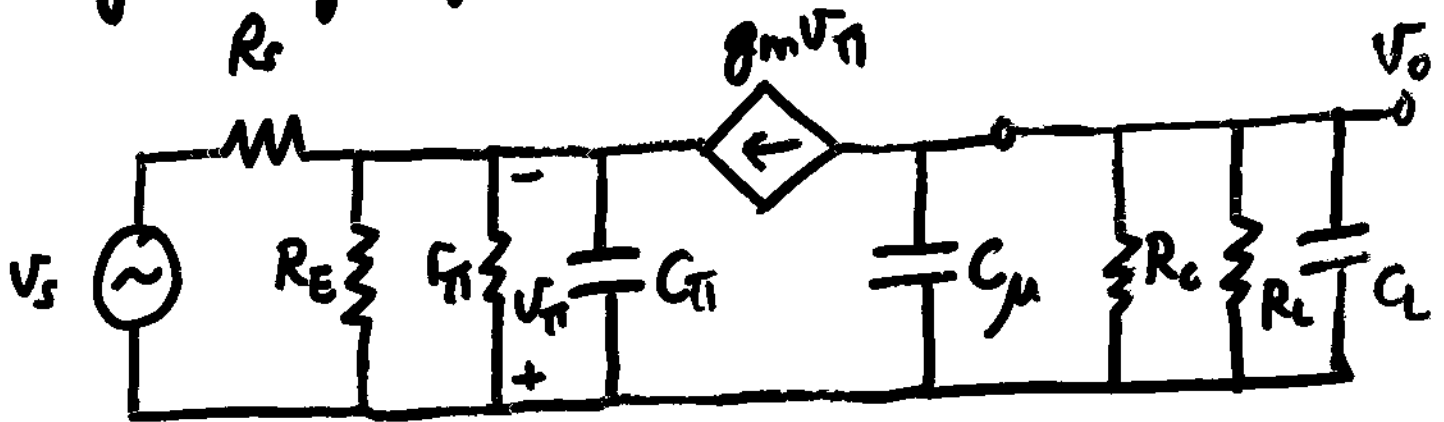


Common Base Amplifier



High Freq Equiv. Ckt



All capacitances are grounded, no Miller effect

$$\text{Define } R'_L = R_C \parallel R_L, \quad C'_L = C_{\mu} + C_L$$

$$R'_E = R_E \parallel \frac{r_{\pi}}{\beta + 1}$$

$$v_o = -g_m \left(R'_L \parallel \frac{1}{j\omega C'_L} \right)$$

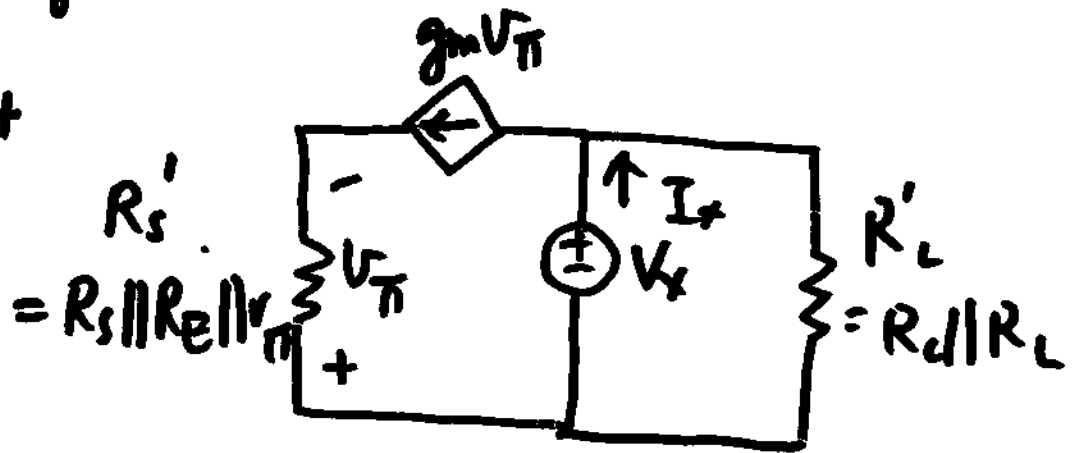
$$v_{\pi} = - \left(\frac{R'_E \parallel \frac{1}{j\omega C_{\pi}}}{R'_E \parallel \frac{1}{j\omega C_{\pi}} + R_s} \right) v_s$$

$$A_{v_s} = g_m \left(R'_L \parallel \frac{1}{j\omega C'_L} \right) \left(\frac{R'_E \parallel \frac{1}{j\omega C_{\pi}}}{R'_E \parallel \frac{1}{j\omega C_{\pi}} + R_s} \right)$$

$$= g_m R'_L \frac{R'_E}{R'_E + R_s} \left(\frac{1}{1 + j\omega R'_L C'_L} \right) \times$$
$$\left(\frac{1}{1 + j\omega (R'_E \parallel R_s) C_{\pi}} \right)$$

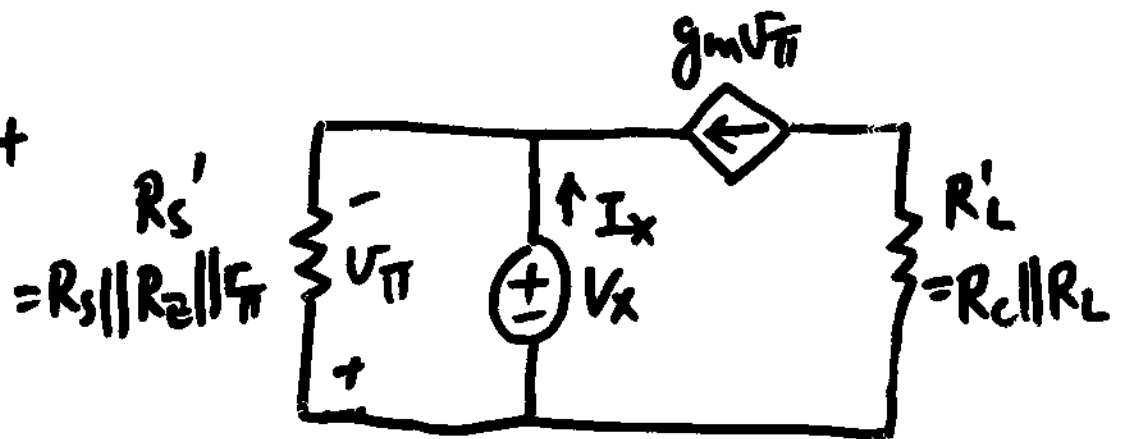
Thevenin Equiv. Resistance

R_{μ} circuit



$$R_{\mu} = R_c || R_L$$

R_{π} circuit



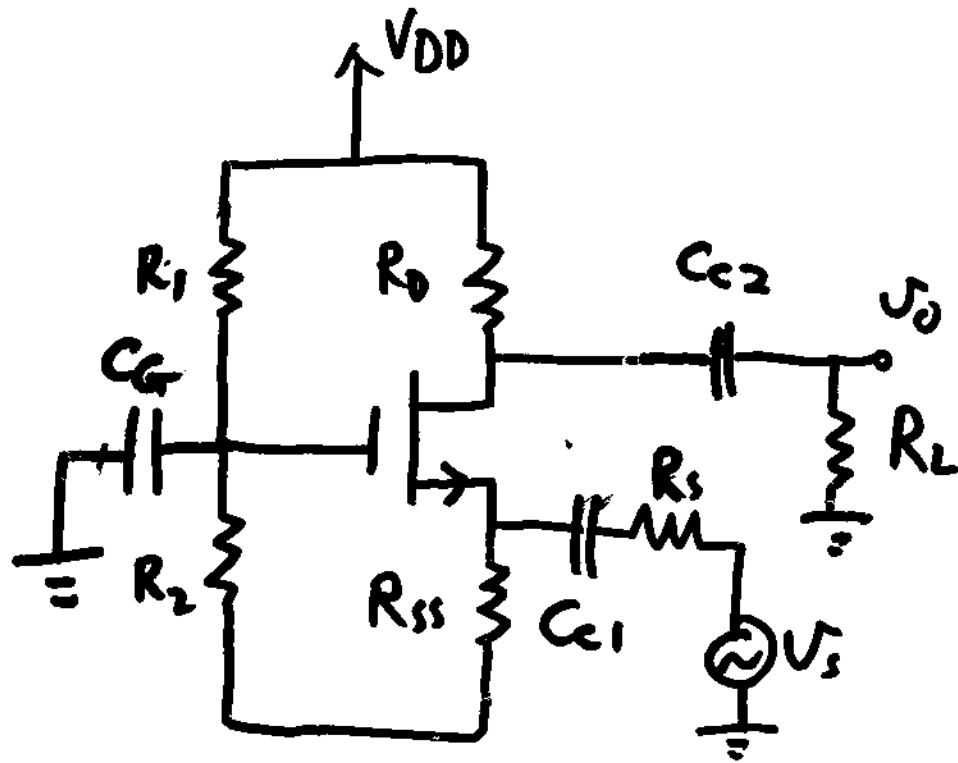
$$I_x = \frac{V_x}{R_s'} + g_m V_x$$

$$R_{\pi} = R_s || R_E || r_{\pi} || \frac{1}{g_m} = R_s || R_E || \frac{r_{\pi}}{\beta + 1}$$

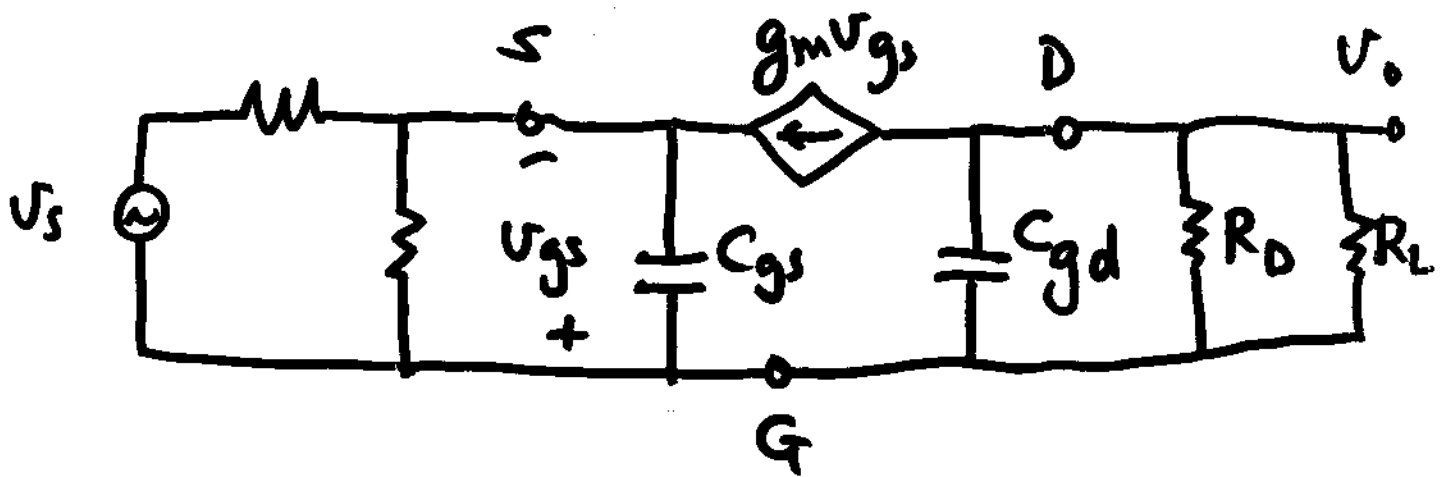
R_{CL} circuit $\equiv R_{\mu}$ circuit

$$R_{CL} = R_c || R_L$$

Common gate Amplifier



High freq. equiv. ckt



$$R_{gs} = R_s \parallel R_{ss} \parallel \frac{1}{g_m}$$

$$\tau_{gs} = (R_s \parallel R_{ss} \parallel \frac{1}{g_m}) C_{gs}$$

$$R_{gd} = R_D \parallel R_L$$

$$\tau_{gd} = (R_D \parallel R_L) C_{gd}$$

$$\omega_H \cong \frac{1}{\tau_{gd} + \tau_{gs}}$$

With C_L

$$R_{CL} = R_D \parallel R_L$$

$$\tau_{CL} = (R_D \parallel R_L) C_L$$

$$\omega_H \cong \frac{1}{\tau_{gd} + \tau_{gs} + \tau_{CL}}$$

Typically, $(\tau_{gd} + \tau_{CL})$ dominates

$$\omega_H \cong \frac{1}{(R_D \parallel R_L)(C_{gd} + C_L)}$$

$$\omega_H \cdot |A_{V_i}| = \frac{g_m}{C_{gd} + C_L}$$

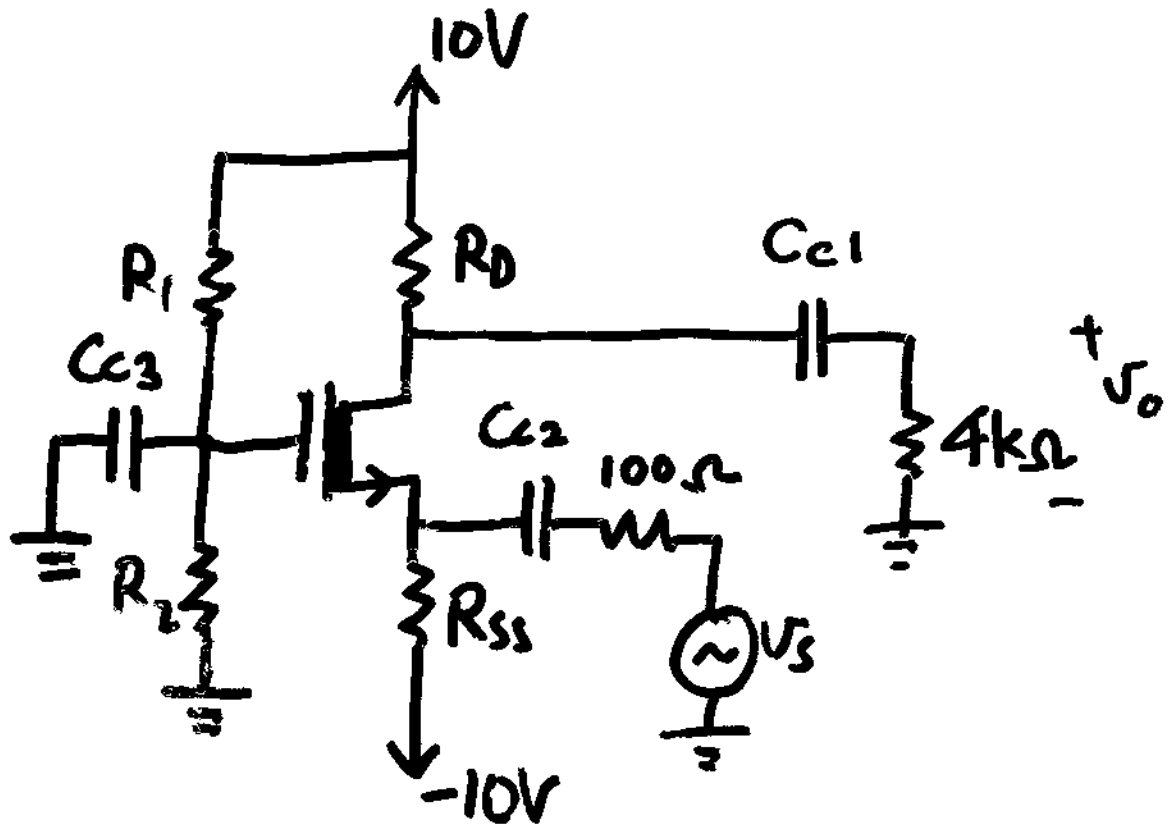
NOT CONSTANT

Depends on
 I_D

Common-Gate Amplifier Design

$$f_L \leq 200\text{Hz} \quad f_H \geq 25\text{MHz}$$

Given $V_{DD} = 10\text{V}$, $I_D = 1\text{mA}$, $k_N = 0.25 \frac{\text{mA}}{\text{V}^2}$
 $V_{TH} = -2\text{V}$



$$C_{gs} = 5\text{pF}$$

$$C_{gd} = 2\text{pF}$$

Solve around the transistor:

$$1\text{mA} = \frac{1}{4} (V_{GS} + 2)^2, \quad g_m = 2K_n (V_{GS} - V_{TH})$$

$$V_{GS} = -4 \text{ or } \underline{\underline{0V}} \quad = 1\text{mA/V}$$

Pick $V_G = 2V$

$$V_{R_{SS}} = 12V \Rightarrow \boxed{R_{SS} = 12k\Omega}$$

$$V_{DS} \geq V_{GS} - V_{TH} = 2V \text{ for SAT}$$

$$\Rightarrow R_D \leq 6k\Omega$$

Pick $\boxed{R_D = 4k\Omega} \Rightarrow V_{DS} = 4V$

$$\begin{aligned} \hookrightarrow A_{v_i} &= +g_m (2000) \\ &= 2V/V \end{aligned}$$

$$V_{R_2} = 2V, \quad V_{R_1} = 8V$$

Pick $\boxed{R_1 = 400k\Omega, \quad R_2 = 100k\Omega}$

Check for $f_L \leq 200 \text{ Hz}$

$$\tau_{cc1} = (R_L + R_D) C_{C1} = 8000 C_{C1}$$

$$\tau_{cc2} = (R_S + R_{SS} // \frac{1}{g_m}) C_{C2}$$

$$= 1023 C_{C2}$$

$$\tau_{cc3} = (R_1 // R_2) C_{C3}$$

$$= 80000 C_{C3}$$

Pick $\omega_{cc2} = 150 \text{ Hz} \Rightarrow C_{C2} = \frac{1}{2\pi(150)(1023)}$
 $= 1.0 \mu\text{F}$

$$\omega_{cc1} = 40 \text{ Hz} \Rightarrow C_{C1} = 0.5 \mu\text{F}$$

$$\omega_{cc3} = 1 \text{ Hz} \Rightarrow C_{C3} = 2 \mu\text{F}$$

$\omega_L \leq 191 \text{ Hz}$

Check for $\omega_H \geq 25 \text{ MHz}$

$$\tau_{gd} = (R_D \parallel R_L) C_{gd}$$

$$= 4 \text{ ns}$$

$$\tau_{gs} = (R_s \parallel R_{ss} \parallel \frac{1}{g_m}) C_{gs}$$

$$= 0.45 \text{ ns}$$

$$\omega_H = \frac{1}{\tau_{gd} + \tau_{gs}} = 225 \text{ Mrad/s}$$
$$\approx \underline{\underline{36 \text{ MHz}}}$$